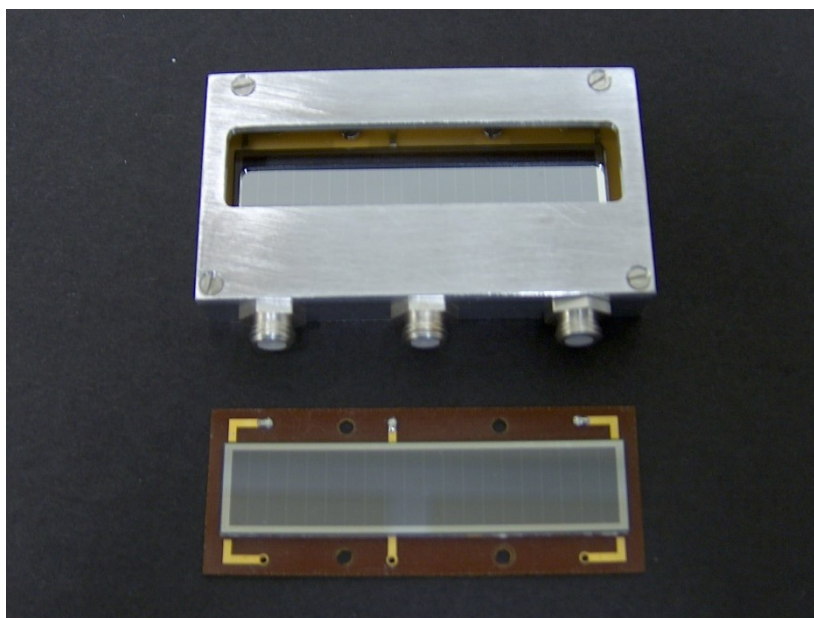


SPECIALIST DETECTORS FOR NUCLEAR PHYSICS

SILICON DETECTOR TYPE:	TOTALLY DEPLETED PLANAR STRUCTURE
DESIGN:	Silicon planar ion implanted structure p on n silicon totally depleted with resistive p junction layer featuring high uniformity and equipotential channel along the linear axis between the two anodes of this common cathode device.
TECHNOLOGY:	4 INCH SILICON
JUNCTION WINDOW:	PSD
OHMIC WINDOW:	2M
POSITION SENSITIVE:	1 axis
N ^o of DETECTORS:	1 or 2
ACTIVE AREA:	50 x 10 mm ²
CAPITANCE (FD):	40-20 pF/cm subject to depletion depth
INTER ANODE RESISTANCE:	4 k Ω minimum – 10 k Ω maximum
ENTRANCE/EXIT WINDOW:	0.2 μ m
THICKNESS:	35 μ m, 65 μ m, 140 μ m, 300 μ m, 500 μ m and 1000 μ m
ALPHA RESOLUTION:	0.5 %
POSITON RESOLUTION:	100 μ m - 300 μ m subject to readout electronics.
OPERATING VOLTAGE:	10 – 250 V subject to thickness chosen
PACKAGES:	Single or double detector PCB available with metal frame. Detector assembly also available in a UHV package design.
CONNECTORS:	Conhex / 3 per detector unless PCB only



Design T PSD/2M single PCB assembly and metal frame assembly.

NOTE: See also Design TT Series, position sensitive detectors (PSD) 18 x 10 mm².

QUALITY ASSURANCE: ISO9001